

February 1998

Features

- **Typical Propagation Delay:** 6ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$, Fastest Part in QMOS Line
- **Wide Operating Temperature Range . . .** $-55^\circ C$ to $125^\circ C$
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HCU Types**
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 20\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}**

Description

The Harris CD74HCU04 unbuffered hex inverter utilizes silicon-gate CMOS technology to achieve operation speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. These devices are especially useful in crystal oscillator and analog applications. Figures 10 and 11 are supplied as design information for the above applications.

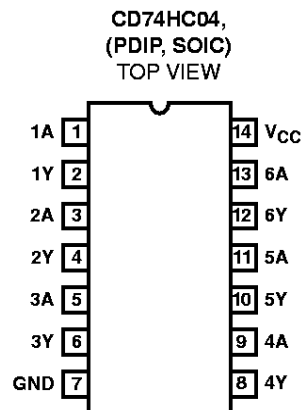
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HCU04E	-55 to 125	14 Ld PDIP	E14.3
CD74HCU04M	-55 to 125	14 Ld SOIC	M14.15

NOTES:

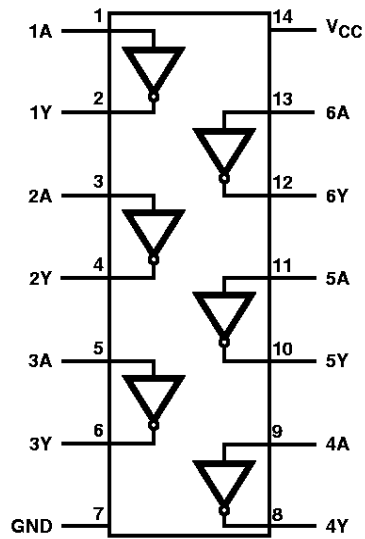
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout



CD74HCU04

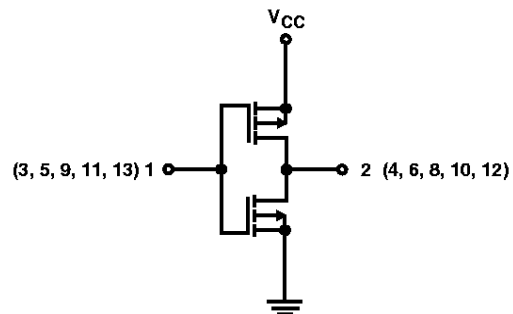
Functional Diagram



Logic Symbol



Schematic Diagram



CD74HCU04

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to +7V
Voltages Referenced to Ground	
DC Input Diode Current, I_{IK}	± 20 mA
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	
DC Output Diode Current, I_{OK}	± 20 mA
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	
DC Drain Current, per Output, I_O	± 25 mA
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	
DC V_{CC} or Ground Current, I_{CC}	± 50 mA

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} ($^{\circ}C/W$)
PDIP Package	100
SOIC Package	180
Maximum Junction Temperature (Hermetic Package or Die)	175 $^{\circ}C$
Maximum Junction Temperature (Plastic Package)	150 $^{\circ}C$
Maximum Storage Temperature Range	-65 $^{\circ}C$ to 150 $^{\circ}C$
Maximum Lead Temperature (Soldering 10s)	300 $^{\circ}C$
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range T_A	-55 $^{\circ}C$ to 125 $^{\circ}C$
Supply Voltage Range, V_{CC}	.2V to 6V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25 $^{\circ}C$		-40 $^{\circ}C$ TO +85 $^{\circ}C$		-55 $^{\circ}C$ TO 125 $^{\circ}C$		UNITS
		V_I (V)	I_O (mA)		MIN	MAX	MIN	MAX	MIN	MAX	
High Level Input Voltage	V_{IH}	-	-	2	1.7	-	1.7	-	1.7	-	V
				4.5	3.6	-	3.6	-	3.6	-	V
				6	4.8	-	4.8	-	4.8	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	0.3	-	0.3	-	0.3	V
				4.5	-	0.8	-	0.8	-	0.8	V
				6	-	1.1	-	1.1	-	1.1	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.8	-	1.8	-	1.8	-	V
			-0.02	4.5	4	-	4	-	4	-	V
			-0.02	6	5.5	-	5.5	-	5.5	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{CC} or GND	-4	4.5	3.98	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	0.2	-	0.2	-	0.2	V
			0.02	4.5	-	0.5	-	0.5	-	0.5	V
			0.02	6	-	0.5	-	0.5	-	0.5	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{CC} or GND	4	4.5	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	± 0.1	-	± 1	-	± 1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	2	-	20	-	40	μA

CD74HCU04

Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Propagation Delay, Input to Output Y (Figure 1)	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	-	70	-	90	-	105	ns
		$C_L = 50\text{pF}$	4.5	-	-	14	-	18	-	21	ns
		$C_L = 15\text{pF}$	5	-	5	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	12	-	15	-	18	ns
Transition Times (Figure 1)	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	-	75	-	95	18	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_i	-	See Figure 3							pF	
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	14	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per inverter.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms

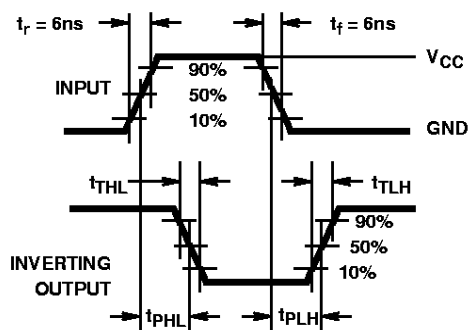


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

Typical Performance Curves

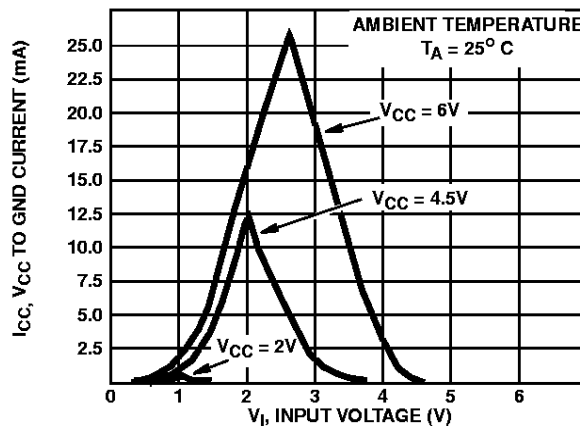


FIGURE 2. TYPICAL INVERTER SUPPLY CURRENT AS FUNCTION OF INPUT VOLTAGE

Typical Performance Curves (Continued)

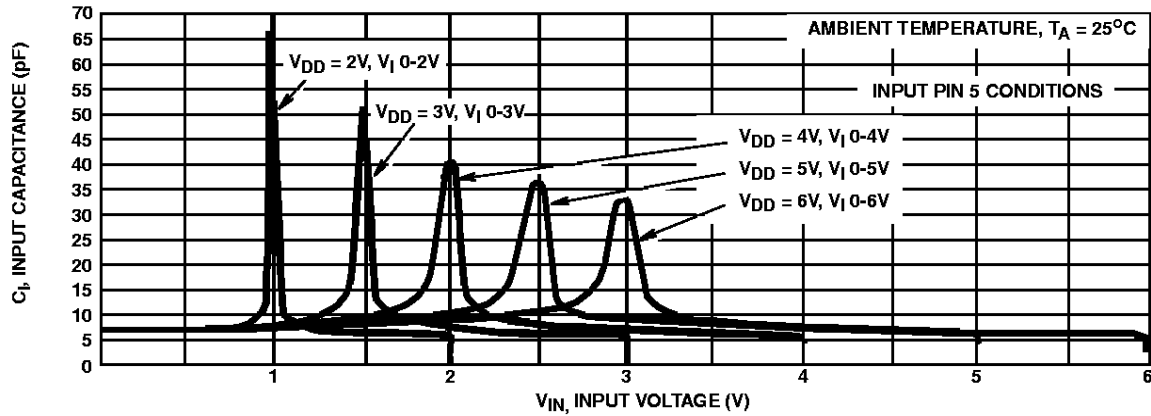


FIGURE 3. INPUT CAPACITANCE AS A FUNCTION OF INPUT VOLTAGE

All Harris Semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

Harris Semiconductor products are sold by description only. Harris Semiconductor reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Harris is believed to be accurate and reliable. However, no responsibility is assumed by Harris or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Harris or its subsidiaries.

Sales Office Headquarters

For general information regarding Harris Semiconductor and its products, call **1-800-4-HARRIS**

NORTH AMERICA

Harris Semiconductor
 P. O. Box 883, Mail Stop 53-210
 Melbourne, FL 32902
 TEL: 1-800-442-7747
 (407) 729-4984
 FAX: (407) 729-5321

EUROPE

Harris Semiconductor
 Mercure Center
 100, Rue de la Fusee
 1130 Brussels, Belgium
 TEL: (32) 2.724.2111
 FAX: (32) 2.724.22.05

ASIA

Harris Semiconductor PTE Ltd.
 No. 1 Tannery Road
 Cencon 1, #09-01
 Singapore 1334
 TEL: (65) 748-4200
 FAX: (65) 748-0400

